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INFORMATION DISCLOSURE STATEMENT BY APPLICANT

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Sheet 1 of 1

PTO/SB/08A (08-03)

Approved for use through 07/31/2006. OMB 0651-0031

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Complete if Known

Application Number	10/691,353
Filing Date	October 22, 2003
First Named Inventor	KRYLIOUK et al.
Art Unit	2879-2823
Examiner Name	H. LEE
Attorney Docket Number	5853-415

U. S. PATENT DOCUMENTS

Examiner Initials*	Cite No. ¹	Document Number	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
		Number-Kind Code ² (if known)			
Lee		US- 6,030,886	02/29/2000	Yuri et al.	
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FOREIGN PATENT DOCUMENTS

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		Country Code ⁴ -Number ⁵ -Kind Code ⁶ (if known)				

Examiner Signature	<i>Heon Min Lee</i>	Date Considered	4/5/2005
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Substitute for form 1449/PTO INFORMATION DISCLOSURE STATEMENT BY APPLICANT (Use as many sheets as necessary)		Complete if Known	
		Application Number	10/691,353
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		Examiner Name	H. Lee
Sheet 1	of 2	Attorney Docket Number	5853-415

NON PATENT LITERATURE DOCUMENTS			
Examiner Initials*	Cite No. ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T ²
Lee		PEARTON et al., "GaN: Processing, defects, and devices," Journal of Applied Physics, 86:1-78, 1999.	
		PEARTON et al., "Fabrication and performance of GaN electronic devices," Materials Science and Engineering: R: Reports, 30:1-137, 2000.	
		KIM et al., "Growth of high-quality GaN on Si(111) substrate by ultrahigh vacuum chemical vapor deposition," Applied Physics Letters, 78:2858-2860, 2001.	
		KROST et al., "GaN-Based Devices on Si," Phys. Stat. Sol., 194:361-375, 2002.	
		WANG et al., "Growth of hexagonal GaN on Si(111) coated with a thin flat SiC buffer layer," Applied Physics Letters, 77:1846-1848, 2000.	
		ZAMIR, "The effect of AlN buffer layer on GaN grown on (111)-oriented Si substrates by MOCVD," Journal of Crystal Growth, 218:181-190, 2000.	
		UEDA et al., "Vapor phase epitaxy growth of GaN on pulsed laser deposited ZnO buffer layer," Journal of Crystal Growth, 187:340-346, 1998.	
		GU et al., "Role of interfacial compound formation associated with the use of ZnO buffers layers in the hydride vapor phase epitaxy of GaN," Applied Physics Letters, 76:3454-3456, 2000.	
		MOLNAR et al., "Growth of gallium nitride by hydride vapor-phase epitaxy," Journal of Crystal Growth, 178:147-156, 1997.	
Lee		DETCHPROHM et al., "Hydride vapor phase epitaxial growth of a high quality GaN film using a ZnO buffer layer," Appl. Phys. Lett., 61:2688-2690, 1992.	

Examiner Signature	<i>Kevin Ming Lee</i>	Date Considered	4/5/2005
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Sheet 2	of 2	Attorney Docket Number	5853-415

NON PATENT LITERATURE DOCUMENTS			
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Lee		STRITTMATTER et al., "LP-MOCVD growth of GaN on silicon substrates-comparison between AlAs and ZnO nucleation layers," Materials Science and Engineering, 59:29-32, 1999.	
		LEE et al., "The Application of a Low Temperature GaN Buffer Layer to Thick GaN Film Growth on ZnO/Si Substrate," Phys. Stat. Sol., 176:583-587, 1999.	
		DEHOFF, R., "Thermodynamics in Materials Science," McGraw Hill, 326-327, 1993.	
Lee		MOLNAR et al., "GALLIUM NITRIDE THICK FILMS GROWN BY HYDRIDE VAPOR PHASE EPITAXY," Mat. Res. Soc. Symp., 423:221-226, 1996.	

Examiner Signature	<i>Kevin Ming Lee</i>	Date Considered	4/5/2005
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